

SavantIC Semiconductor

Product Specification

Silicon NPN Power Transistors 2N5622 2N5624 2N5626 2N5628

DESCRIPTION

- With TO-3 package
- Excellent safe operating area
- Low collector saturation voltage

APPLICATIONS

- For audio and general-purpose applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

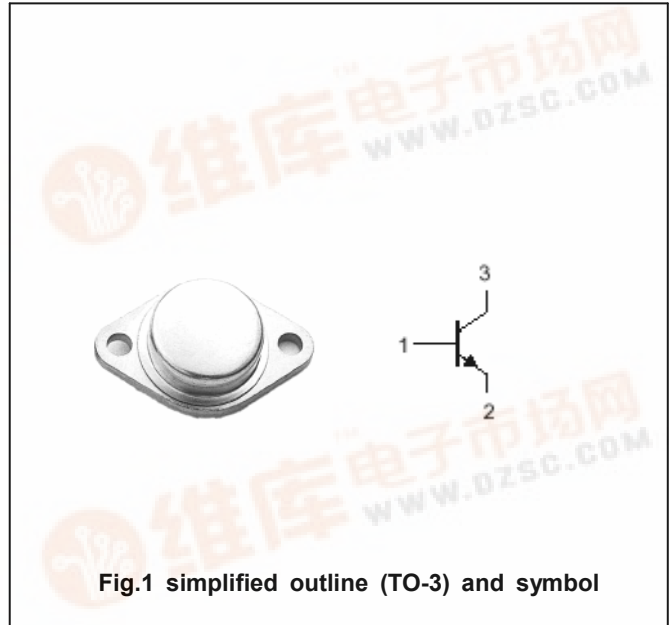


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	2N5622	Open emitter	80	V
		2N5624/5626		100	
		2N5628		120	
V_{CEO}	Collector-emitter voltage	2N5622	Open base	60	V
		2N5624/5626		80	
		2N5628		100	
V_{EBO}	Emitter-base voltage		Open collector	5	V
I_C	Collector current			10	A
P_D	Total power dissipation		$T_C = 25\square$	100	W
T_j	Junction temperature			150	$\square$
T_{stg}	Storage temperature			-65~200	$\square$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	1.5	$\square/W$

Silicon NPN Power Transistors 2N5622 2N5624 2N5626 2N5628

CHARACTERISTICS**T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER		CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	2N5622	$I_C=50mA ; I_B=0$	60			V
		2N5624/5626		80			
		2N5628		100			
V_{CEsat}	Collector-emitter saturation voltage		$I_C=10A ; I_B=1A$			1.5	V
V_{BE}	Base-emitter on voltage		$I_C=5A ; V_{CE}=5V$			1.5	V
I_{CBO}	Collector cut-off current		$V_{CB}=\text{Rated } V_{CBO} ; I_E=0$			0.1	mA
I_{EBO}	Emitter cut-off current		$V_{EB}=5V ; I_C=0$			0.1	mA
h_{FE}	DC current gain	2N5622/5626	$I_C=5A ; V_{CE}=5V$	70		200	
		2N5624/5628		30		90	
f_T	Transition frequency	2N5622/5626	$I_C=1A ; V_{CE}=12V$	40			MHz
		2N5624/5628		30			

PACKAGE OUTLINE

